

**FORM PTO-1449**
**LIST OF PATENTS AND OTHER ITEMS  
FOR APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT**

(Use several sheets if necessary)

**ATTY. DOCKET NO.**  
0180144

**SERIAL NO.**  
10/643,461

**APPLICANTS:**  
Xiang, et al.

**FILING DATE:**  
August 18, 2003

**GROUP ART:**  
2815
**U.S. PATENT DOCUMENTS**

| Exam. Initials |   | DOCUMENT NUMBER | DATE      | NAME             | CLASS | SUB CLASS | FILING DATE |
|----------------|---|-----------------|-----------|------------------|-------|-----------|-------------|
| /PB/           | 1 | 6,262,462       | 7/17/2001 | Marshall, et al. |       |           |             |
| /PB/           | 2 | 5,721,145       | 2/24/1998 | Kusakabe, et al. |       |           |             |
| /PB/           | 3 | 2002/093046 A1  | 7/18/2002 | Moriya, et al.   |       |           |             |

**FOREIGN PATENT DOCUMENTS**

| Exam. Initials |   | DOCUMENT NUMBER   | PUBLICATION DATE | COUNTRY OR PATENT OFFICE | CLASS | SUB CLASS | TRANSLATION |    |
|----------------|---|-------------------|------------------|--------------------------|-------|-----------|-------------|----|
|                |   |                   |                  |                          |       |           | YES         | NO |
| /PB/           | 1 | WO 2004/112147 A1 | 12/23/2004       | WIPO                     |       |           |             |    |
| /PB/           | 2 | EP 1 164 636 A2   | 12/19/2001       | EPO                      |       |           |             |    |
| /PB/           | 3 | JP 05082777       | 4/2/1993         | JPO                      |       |           |             |    |

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)**

|      |   |   |
|------|---|---|
| /PB/ | 1 | Ota et al, <i>Novel Locally Strained Channel Technique for High Performance 55nm CMOS</i> , IEDM Technical Digest, 27-30 (2002)   |
| /PB/ | 2 | <i>Applying Mechanical Stress to Improve MOS Semiconductor Performance</i> , 30 IBM Technical Disclosure Bulletin, 330-333 (1988)   |
| /PB/ | 3 | Momose et al, <i>Relationship Between Mobility and Residual-Mechanical-Stress As Measured By Raman Spectroscopy For Nitrided-Oxide-Gate MOSFETs</i> , 90 IEDM, 65-68 (1990) |
| /PB/ | 4 | Jennifer O'Connor, <i>Analytical Predictions of Thermal Stress in MOSFETs</i> , IEEE, 131-143 (1995)  |
| /PB/ | 5 | Wristers et al, <i>Ultra Thin Oxide Reliability: Effects of Gate Doping Concentration and Poly-Si/SiO<sub>2</sub> Interface Stress Relaxation</i> , IEEE, 77-83 (1996)      |
| /PB/ | 6 | Steegen et al, <i>Silicide-induced Stress In Si: Origin and Consequences for MOS Technologies</i> , 38 Materials Science and Engineering R: Reports, 1-53 (2002)            |

**EXAMINER:** /Paul Budd/**DATE CONSIDERED:** 11/23/2010

**EXAMINER:** Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.

Information Disclosure Statement-- Section 9 PTO-1449